

Amendments to the Specification

Page 6, after line 6, insert the following text:

FIG. 13 is a schematic cross-sectional view of a modification of the first embodiment.

Page 8, beginning with line 26, please delete the paragraph and replace with the following text:

It is preferred that the resin mater **3** used as the pressure holding means has a coefficient of linear expansion greater than a material of the substrate **1**. Concretely, it is preferred that a difference in coefficient of linear thermal expansion (linear expansion) between the resin material and the substrate material (= the projection **11** for the first bump **10**) is within a range of $5 \times 10^{-6} / ^\circ\text{C}$ to $6 \times 10^{-6} / ^\circ\text{C}$. When the difference is less than $5 \times 10^{-6} / ^\circ\text{C}$, the required contact pressure described above may not be obtained. On the other hand, when the difference is more than $60 \times 10^{-6} / ^\circ\text{C}$, distortion occurs between the cured resin mater **3c** and the substrate **1** or the semiconductor chip **2** because of excessive shrinkage caused in every directions by curing of the resin material, so that the adhesion strength there between may lower.

Page 10, beginning with line 10, please delete the paragraph and replace with the following text:

To further improve adhesion between the first bump **10** and the second bump **20**, it is preferred that one of the first and second bumps has a surface layer of a material selected from tin and tin alloys, and the other one has a gold layer. In this case, as shown in FIG. 13, a solid state diffusion layer 25 of tin and gold is formed at the interface between the first and second bumps (10, 20d). For example, this sold state diffusion layer can be generated at a temperature of 150 to 200 °C under the pressure.

Page 22, beginning with line 8, please delete the paragraph and replace with the following text:

Next, as shown in FIG. 10C, the second substrate **100** is molded on the first substrate **1** by injection molding such that a part of the first substrate is encapsulated in the second substrate. In this embodiment, the second substrate **100** is molded such that a part of the conductive pattern **19** on the extended top surface of the first substrate **1** is exposed. Since the contact pressure between the first bumps **10** and the second bumps **20** is increased through the pressure holding member **4** by a shrinkage caused by curing of the resin material of the second substrate **100**, it is possible to further improve the reliability of the electrical connections between those bumps. In the present embodiment, a conductive layer **120** of one of first bumps ~~120~~ 110 of the second substrate **100** is extended along a side of the second substrate to make an electrical connection between the conductive pattern **19** on the first substrate **1**.